

## 10G EPON OLT BOSA(10G1577T 10G1270R)

#### Description

- LD: 10G EML 7pin APD-TIA: 10G 6pin
- Mode of Fiber: SM
- Product structure note: SC/PC receptacle, Machining housing structure, receiver sealed with epoxy, with Isolator.

#### **Absolute Maximum Ratings:**

Parameter	Symbol	Min.	Max.	Unit						
Storage Temperature	Tstg	-40	85	°C						
Operating Temperature	Tcase	-5	75	°C						
Soldering Temperature	Tsld		260<10s	°C						
10G 1577nm EML Transmitter										
EML LD Reverse Voltage	V <sub>RL</sub>	ł	2	V						
EML LD Forward Current	lf		150	mA						
EA Reverse Voltage	Vm	-3	1	V						
EML MPD Reverse Voltage	Vmon		20	V						
EML MPD Forward Current	Imon		2	mA						
TEC Cooling Voltage	VTEC		1.45	V						
TEC Cooling Current	ITEC		0.8	А						
10G 1270nm APD Receiver										
Storage Temperature	Tstg	-40	85	°C						
Reverse Current	IR		2	mA						
ESD Susceptibility	ESD		150	V						
Lead Soldering (Temperature)/(Time)			260/10	°C/Sec						

## **Electrical and Optical Characteristics – Transmitter:**

Unless otherwise specified, the specifications below are defined at TC=25±3  $^\circ \! \mathbb{C}$ 

Parameter	Symbol	Min.	Тур.	Max.	Unit	Note	
Laser Operating Temperature	Tld		45		°C	CW, lop=lth+20mA, Tc=25°C	
Threshold Current	lth		8	40	mA	at Tc=25℃	
Operating Current	lop			115	mA	at Tc=25℃ Pf=6.8dBm	
LD Forward Voltage	Vf			2.5	V	lf=lop	
Center Wavelength	λc	1575	1577	1580	nm	CW, Pop=4ddBm, Tld	
Spectral Wildth(-20dB)	$\triangle \lambda$		0.2	0.4	nm	CW, Pop=4ddBm, Tld	
Side Mode Suppression Ratio	SMSR	35			dB	CW, Pop=4ddBm, Tld	



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Monitor Current	Imon	50		2000	uA	at Tc=25℃ Pf=6.8dBm
Monitor Dark Current	ld			0.1	μA	V <sub>RD</sub> =1V
Thermistor Resistance	Rth	9.5	10	10.5	ΩK	at Tc=25℃ Tld
B constant of Rth	В	3365	3435	3505	К	
Optical Isolation	ISO	30			dB	
Tracking Error	TE	-1.2		1.0	dB	APC, -5/℃+75℃, +75℃/+25℃

### **Electrical / Optical Specifications – Receiver:**

Unless otherwise specified, the specifications below are defined at TC=25±3  $^\circ\!\mathrm{C}$ 

Description	Symbol	Min.	Тур.	Max.	Unit	Note
Operating wavelength	λ		1270		nm	
TIA Supply Voltage	Vcc	3.0	3.3	3.6	V	
Supply Current	lcc		40		mA	
Break Down Voltage	Vbr	22	27	32	V	I <sub>d</sub> =10μΑ
Operating Current	Іор		10		μA	λ=1270nm Pin=-30dBm Vop=Vbr-2V
Sensitivity	Sen			-29	dBm	λ = 1270nm 9.95G ER=6, BER=10 <sup>-3</sup> PRBS=2 <sup>31</sup> -1, V <sub>R</sub> =Vbr-2

### **Mechanical Outline Dimensions and PIN Assignment**

Note : Machining housing structure, receiver sealed with black epoxy.





#### **Marking Requirements**

According to the Sunstar's Marking Requirements of Optical Active Devices ASSY.



#### The Inspection Requirements of End face

According to the International Standard of IPC8497-1.

#### **Appearance and Packaging**

According to the OSM's Specifications of Optical Active Devices Packaging Standard and Management.

#### **Precaution:**

(1) The modules should be handled in the same manner as ordinary semiconductor devices to prevent the electro-static damages. For safe keeping and carrying, the modules should be packaged with ESD proof material. To assemble the modules on PCB, the workbench, the soldering iron and the human body should be grounded.

(2) Please pay special attention to the atmosphere condition because the dew on the module may cause some electrical damages.

(3) Under such a strong vibration environment as in automobile, the performance and reliability are not guaranteed.

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